

## 1. Global joint venture starts operations as WeEn Semiconductors

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Thank you for your cooperation and understanding,

WeEn Semiconductors



**Product data sheet** 

## 1. General description

Ultrafast power diode in a SOD59 (2-lead TO-220AC) plastic package.

## 2. Features and benefits

- · Fast switching
- Guaranteed ESD capability
- High thermal cycling performance
- Low on-state loss
- Low thermal resistance
- Rugged: reverse voltage surge capability
- Soft recovery minimizes power-consuming oscillations

# 3. Applications

Output rectifiers in high-frequency switched-mode power supplies

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>RRM</sub>	repetitive peak reverse voltage			-	-	200	V
I <sub>F(AV)</sub>	average forward current	SQW; $\delta$ = 0.5; $T_{mb} \le 128$ °C; <u>Fig. 1</u> ; <u>Fig. 2</u>		-	-	8	Α
Static characte	eristics						
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 8 A; T <sub>j</sub> = 150 °C; <u>Fig. 4</u>		-	0.8	0.895	V
Dynamic chara	acteristics						
t <sub>rr</sub>	reverse recovery time	$I_F = 1 \text{ A}$ ; $V_R = 30 \text{ V}$ ; $dI_F/dt = 100 \text{ A/s}$ ; $T_j = 25 \text{ °C}$ ; ramp recovery; Fig. 5; Fig. 7		-	20	25	ns
Electrostatic discharge							
V <sub>ESD</sub>	electrostatic discharge voltage	HBM; C = 250 pF; R = 1.5 kΩ		-	-	8	kV





Ultrafast power diode

# 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	mb	K — A
2	Α	anode	}	001aaa020
mb	mb	mounting base; cathode	TO-220AC (SOD59)	

# 6. Ordering information

Table 3. Ordering information

Type number	Package	ge						
	Name	Description	Version					
BYW29E-200	TO-220AC	plastic single-ended package; heatsink mounted; 1 mounting hole; 2-lead TO-220AC	SOD59					

# 7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{RRM}$	repetitive peak reverse voltage		-	200	V
$V_{RWM}$	crest working reverse voltage		-	200	V
$V_R$	reverse voltage		-	200	V
I <sub>F(AV)</sub>	average forward current	SQW; δ = 0.5 ; T <sub>mb</sub> ≤ 128 °C; <u>Fig. 1</u> ; <u>Fig. 2</u>	-	8	А
I <sub>FRM</sub>	repetitive peak forward current	SQW; $\delta$ = 0.5 ; $t_p$ = 25 $\mu$ s; $T_{mb} \le$ 128 °C	-	16	Α
I <sub>FSM</sub>	non-repetitive peak forward	SIN; $t_p = 8.3 \text{ ms}$ ; $T_{j(init)} = 25 \text{ °C}$	-	88	Α
	current	SIN; $t_p$ = 10 ms; $T_{j(init)}$ = 25 °C	-	80	Α
I <sub>RRM</sub>	repetitive peak reverse current	$\delta = 0.001$ ; $t_p = 2 \mu s$	-	0.2	Α
I <sub>RSM</sub>	non-repetitive peak reverse current	t <sub>p</sub> = 100 μs	-	0.2	Α
T <sub>stg</sub>	storage temperature		-40	150	°C

BYW29E-200

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Symbol	Parameter	Conditions		Min	Max	Unit	
T <sub>j</sub>	junction temperature			-	150	°C	
Electrostatic d	Electrostatic discharge						
V <sub>ESD</sub>	electrostatic discharge voltage	HBM; C = 250 pF; R = 1.5 kΩ		-	8	kV	

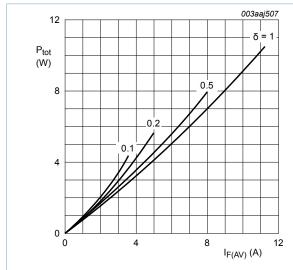


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values

$$\begin{split} I_{F(AV)} &= I_{F(RMS)} \times \sqrt{\delta} \\ V_{O} &= 0.791 \text{ V; } R_{S} = 0.013 \text{ } \Omega \end{split}$$

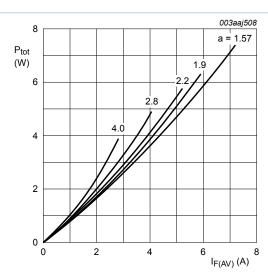


Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

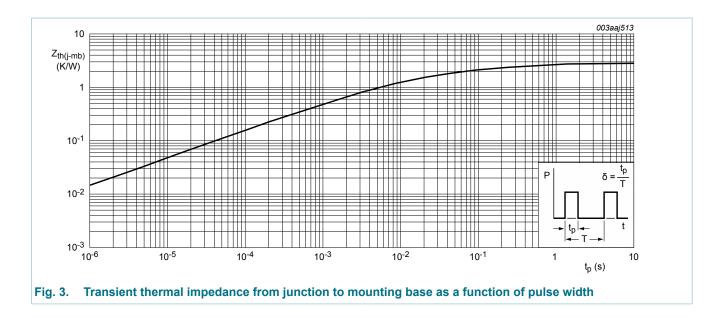
$$\begin{aligned} \mathbf{a} &= \mathbf{form} \ \mathbf{factor} = I_{F(RMS)} / I_{F(AV)} \\ \mathbf{V_O} &= \mathbf{0.791} \ \mathbf{V; R_S} = \mathbf{0.013} \ \Omega \end{aligned}$$

## 8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	Fig. 3	-	-	2.7	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	-	60	-	K/W

### Ultrafast power diode



## 9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics				'	
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 8 A; T <sub>j</sub> = 25 °C; <u>Fig. 4</u>	-	0.92	1.05	V
		I <sub>F</sub> = 20 A; T <sub>j</sub> = 25 °C; <u>Fig. 4</u>	-	1.1	1.3	V
		I <sub>F</sub> = 8 A; T <sub>j</sub> = 150 °C; <u>Fig. 4</u>	-	0.8	0.895	V
I <sub>R</sub>	reverse current	V <sub>R</sub> = 200 V; T <sub>j</sub> = 25 °C	-	2	10	μΑ
		V <sub>R</sub> = 200 V; T <sub>j</sub> = 100 °C	-	0.2	0.6	mA
Dynamic cl	haracteristics					
Q <sub>r</sub>	recovered charge	$I_F = 2 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 20 \text{ A/s};$ $T_j = 25 ^{\circ}\text{C}; Fig. 5; Fig. 6$	-	4	11	nC
t <sub>rr</sub> reverse recovery t		$I_F$ = 1 A; $V_R$ = 30 V; $dI_F/dt$ = 100 A/s; $T_j$ = 25 °C; ramp recovery; <u>Fig. 5</u> ; <u>Fig. 7</u>	-	20	25	ns
		$I_F = 0.5 \text{ A}$ ; $I_R = 1 \text{ A}$ ; $I_{R(meas)} = 0.25 \text{ A}$ ; $I_j = 25 \text{ °C}$ ; step recovery; Fig. 8	-	15	20	ns
$V_{FRM}$	forward recovery voltage	$I_F = 1 \text{ A}; dI_F/dt = 10 \text{ A/s}; T_j = 25 °C;$ Fig. 9	-	1	-	V

#### **Ultrafast power diode**

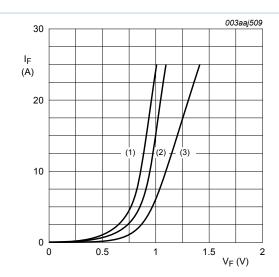


Fig. 4. Forward current as a function of forward voltage

(1)  $T_i = 150$  °C; typical values;

(2)  $T_i = 150$  °C; maximum values;

(3)  $T_i = 25$  °C; maximum values;

 $V_O = 0.791 \text{ V}; R_S = 0.013 \Omega$ 

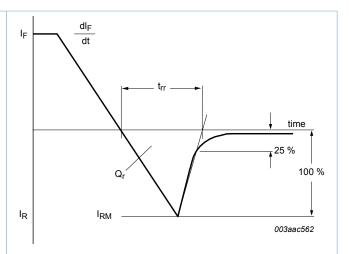


Fig. 5. Reverse recovery definitions; ramp recovery

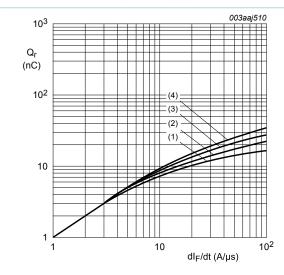


Fig. 6. Recovered charge as a function of rate of change of forward current; maximum values

(1) 
$$I_F = 1 A$$
;  $T_i = 25 \, ^{\circ}\text{C}$ 

(2) 
$$I_F = 2 A$$
;  $T_j = 25 \, ^{\circ}\mathrm{C}$ 

(3) 
$$I_F = 5 A$$
;  $T_j = 25 \text{ °C}$ 

(4)  $I_F = 10 A; T_i = 25 °C$ 

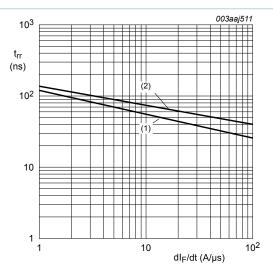
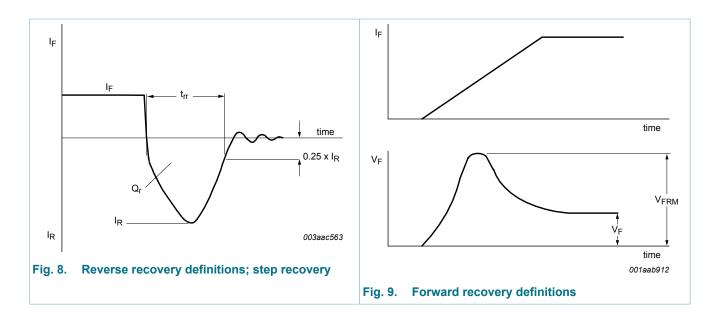


Fig. 7. Reverse recovery time as a function of rate of change of forward current; maximum values

(1) 
$$I_F = 1 A$$
;  $T_i = 25 \, ^{\circ}C$ 

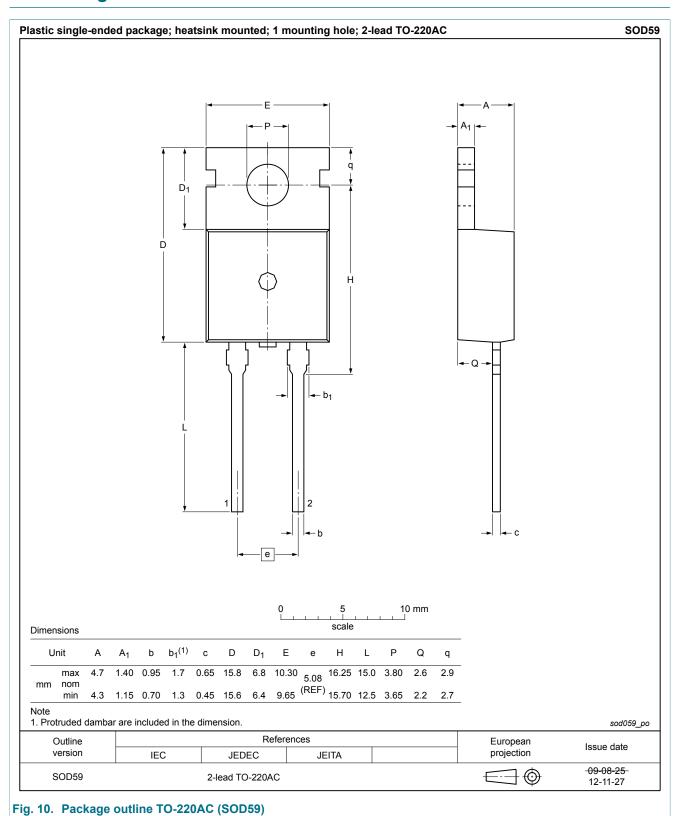
(2) 
$$I_F = 10 \text{ A}; T_j = 25 \text{ }^{\circ}\text{C}$$

### Ultrafast power diode



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# 10. Package outline



#### Ultrafast power diode

## 11. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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